

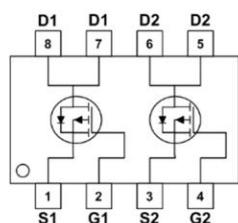
### GENERAL FEATURES

- $V_{DS} = -30V$   $I_D = -8A$
- $R_{DS(ON)} < -22m\Omega$  @  $V_{GS}=10V$
- $R_{DS(ON)} < -26m\Omega$  @  $V_{GS}=4.5V$

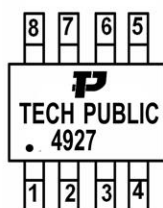
### Package and Pin Configuration



SOP-8 top view



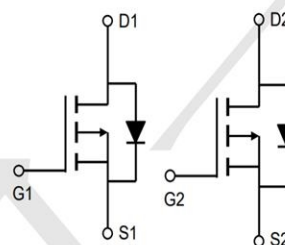
### Marking:



### Application

- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

### Circuit diagram



### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_A=25^\circ C$	Continuous Drain Current <sup>3</sup>	8	A
$I_D@T_A=70^\circ C$	Continuous Drain Current <sup>3</sup>	7	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	40	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	2	W
	Linear Derating Factor	0.016	W/ $^\circ C$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

### Thermal Data

Symbol	Parameter	Value	Unit
$R_{thj-a}$	Thermal Resistance Junction-ambient <sup>3</sup>	Max. 62.5	$^\circ C/W$

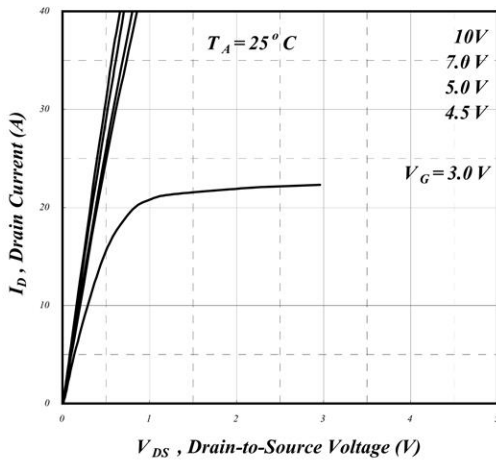
### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	-	-	V
ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	-	0.01	-	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =8A	-	-	22	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	-	-	26	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	-	3	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =8A	-	8	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current (T <sub>j</sub> =25°C)	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V	-	-	25	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±20V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =8A	-	14.5	23	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =24V	-	2.3	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	7.7	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =15V	-	7.2	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =1A	-	8.6	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω, V <sub>GS</sub> =10V	-	24.8	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =15Ω	-	8.6	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	950	1420	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V	-	220	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	160	-	pF
R <sub>g</sub>	Gate Resistance	f=1.0MHz	-	1	1.5	Ω

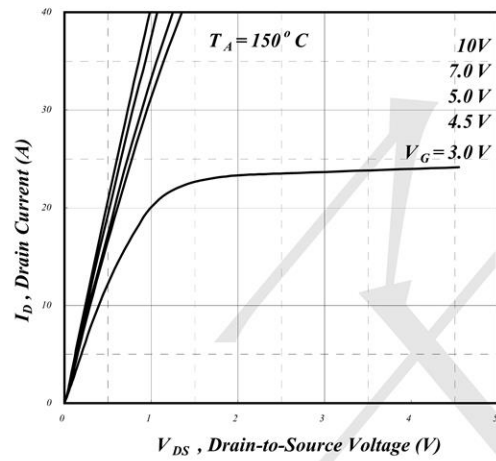
### Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =1.7A, V <sub>GS</sub> =0V	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time <sup>2</sup>	I <sub>S</sub> =8A, V <sub>GS</sub> =0V,	-	25	-	ns
		di/dt=100A/μs	-	21	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	21	-	nC

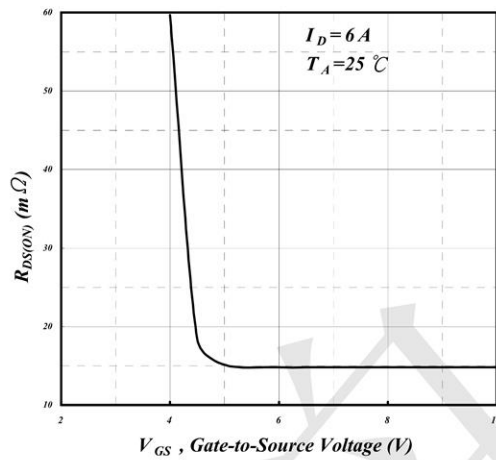
**Typical Electrical and Thermal Characteristics**



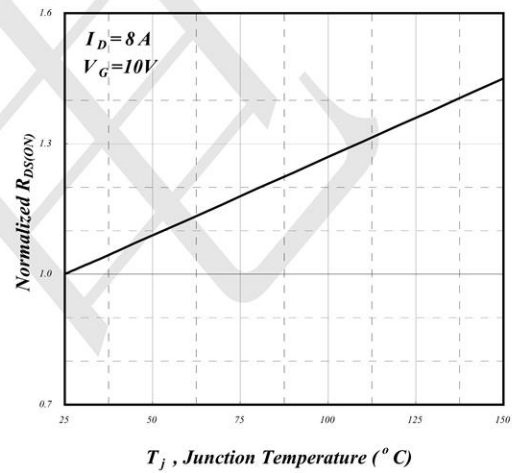
**Fig 1. Typical Output Characteristics**



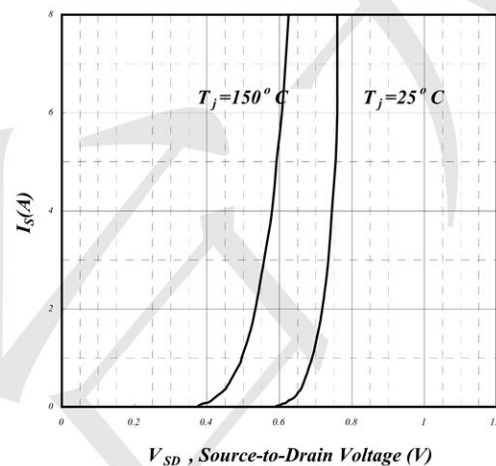
**Fig 2. Typical Output Characteristics**



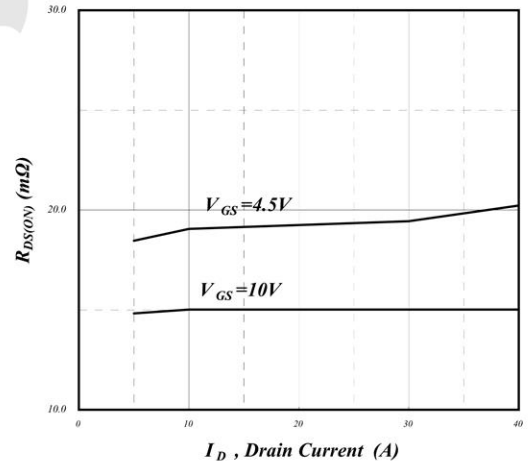
**Fig 3. On-Resistance v.s. Gate Voltage**



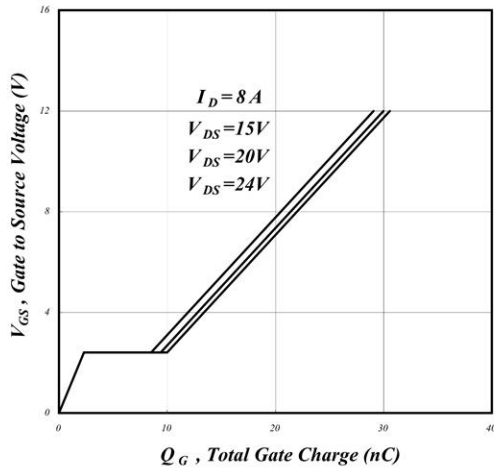
**Fig 4. Normalized On-Resistance v.s. Junction Temperature**



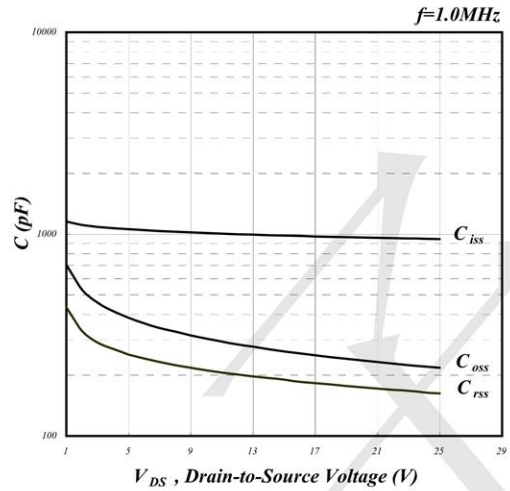
**Fig 5. Forward Characteristic of Reverse Diode**



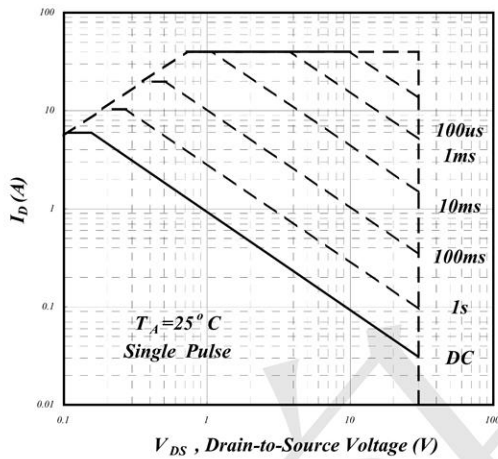
**Fig 6. On-Resistance vs. Drain Current**



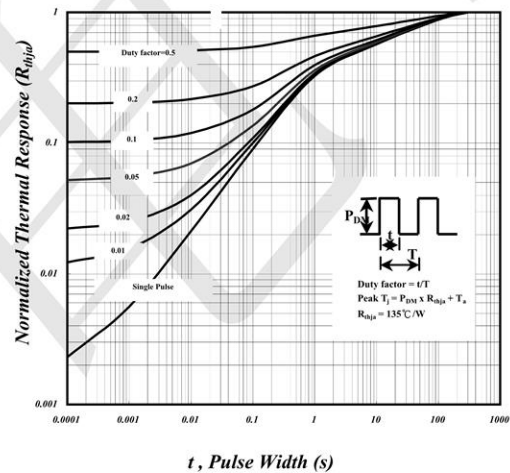
**Fig 7. Gate Charge Characteristics**



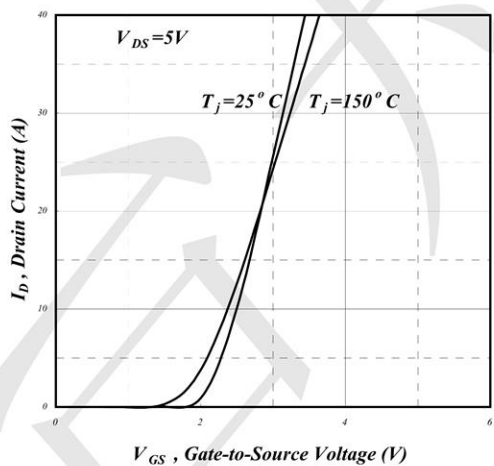
**Fig 8. Typical Capacitance Characteristics**



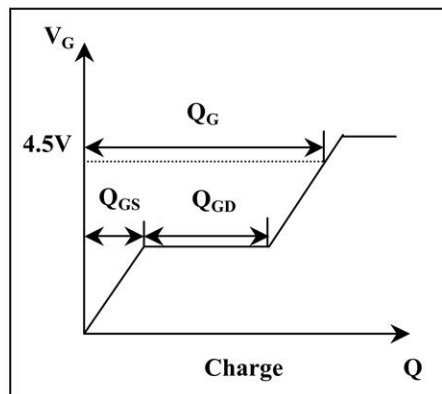
**Fig 9. Maximum Safe Operating Area**



**Fig 10. Effective Transient Thermal Impedance**

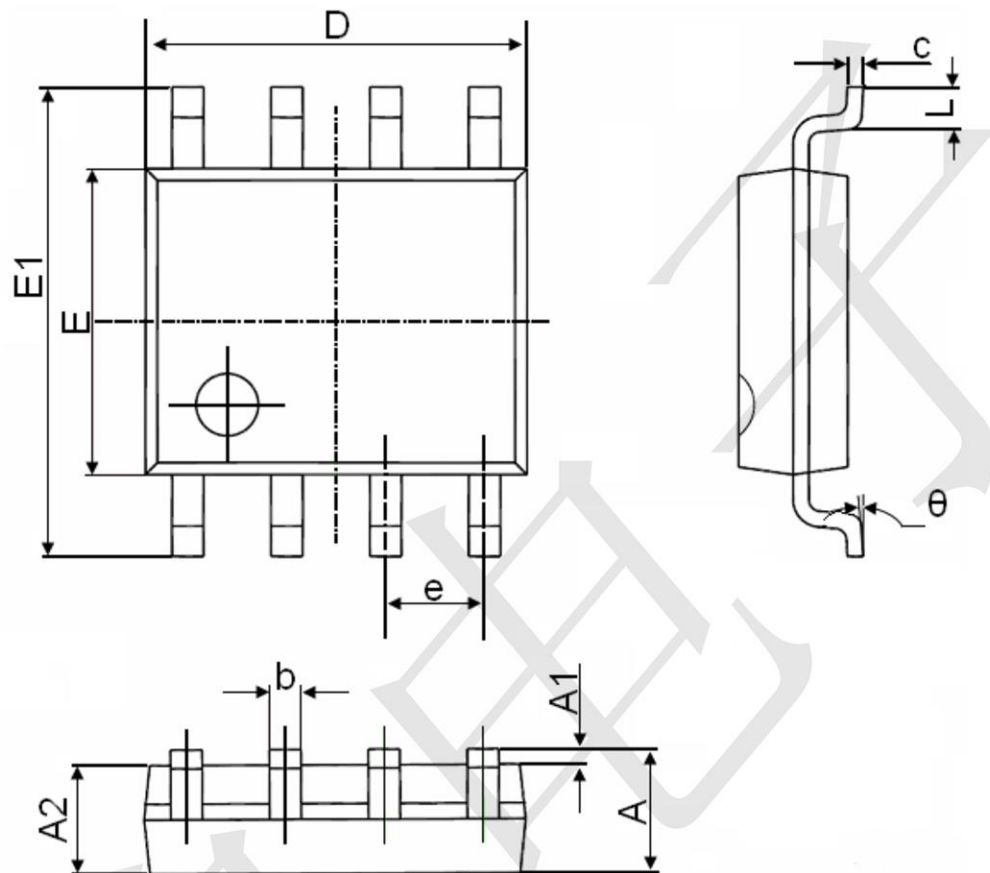


**Fig 11. Transfer Characteristics**



**Fig 12. Gate Charge Waveform**

**SOP-8 Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [MOSFET](#) category:*

*Click to view products by [TECH PUBLIC](#) manufacturer:*

Other Similar products are found below :

[IRFD120](#) [JANTX2N5237](#) [2SK2267\(Q\)](#) [BUK455-60A/B](#) [TK100A10N1,S4X\(S](#) [MIC4420CM-TR](#) [VN1206L](#) [NDP4060](#) [SI4482DY](#)  
[IRS2092STRPBF-EL](#) [IPS70R2K0CEAKMA1](#) [TK31J60W5,S1VQ\(O](#) [TK31J60W,S1VQ\(O](#) [TK16J60W,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#)  
[DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [DMC2700UDMQ-7](#) [DMN2080UCB4-7](#)  
[DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#)  
[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [IPS60R360PFD7SAKMA1](#)  
[DMN2990UFB-7B](#) [SSM3K35CT,L3F](#) [IPLK60R1K0PFD7ATMA1](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [IPWS65R035CFD7AXKSA1](#)  
[MCQ7328-TP](#) [SSM3J143TU,LXHF](#) [DMN12M3UCA6-7](#) [PJMF280N65E1\\_T0\\_00201](#) [PJMF380N65E1\\_T0\\_00201](#)  
[PJMF280N60E1\\_T0\\_00201](#) [PJMF600N65E1\\_T0\\_00201](#) [PJMF900N65E1\\_T0\\_00201](#)